ABSTRACT

Disclosed is a method for providing antistaticity for polymeric, integrated circuit (IC) trays, which allows gaseous ions, such as nitrogen and argon, or metal ions, such as Ti, Li and Al, to be implanted to a surface depth of 1.5 μm in IC trays. In addition to experiencing no dimensional changes during the antistaticity working, the IC trays have a uniform distribution of ions over their surfaces and range, in surface resistance, from 10^6 to 10^{12} Ω/cm^2.

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